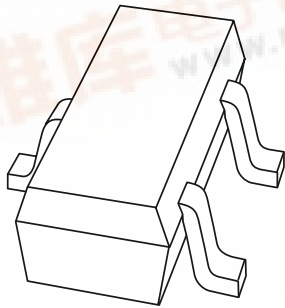


DISCRETE SEMICONDUCTORS

DATA SHEET



PDTC115EE

NPN resistor-equipped transistor;

$R1 = 100 \text{ k}\Omega$, $R2 = 100 \text{ k}\Omega$

Product specification

2002 May 08

**NPN resistor-equipped transistor;
R1 = 100 kΩ, R2 = 100 kΩ**

PDTC115EE

FEATURES

- Built-in bias resistors R1 and R2 (typically 100 kΩ each)
- Simplification of circuit design
- Reduces number of components and required PCB area.

APPLICATIONS

- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configuration without use of external resistors.

DESCRIPTION

NPN resistor-equipped transistor in a SOT416 (SC-75) plastic package.

MARKING

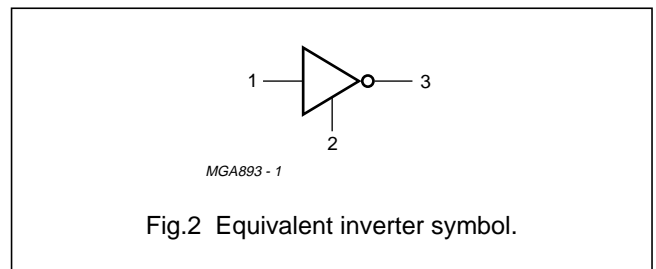
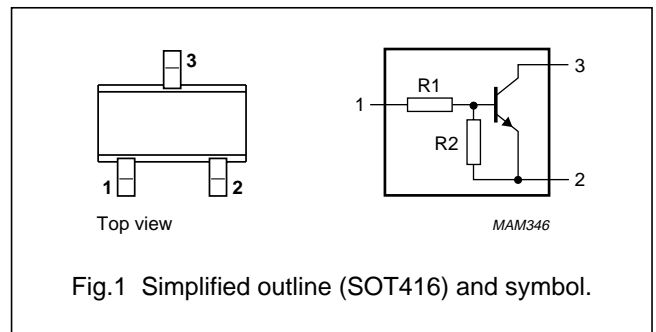
TYPE NUMBER	MARKING CODE
PDTC115EE	46

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	50	V
I _O	output current (DC)	20	mA
R1	bias resistor	100	kΩ
R2	bias resistor	100	kΩ

PINNING

PIN	DESCRIPTION
1	base/input
2	emitter/ground
3	collector/output



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	10	V
V _i	input voltage positive negative		–	+40	V
			–	–10	V
I _O	output current (DC)		–	20	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	150	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Refer to standard SOT416 (SC-75) mounting conditions.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	833	K/W

Note

1. Refer to standard SOT416 (SC-75) mounting conditions.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	–	–	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	–	–	1	μA
		V _{CE} = 30 V; I _B = 0; T _j = 150 °C	–	–	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	–	–	50	μA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA	80	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 300 mA; I _B = 10 mA	–	–	150	mV
V _{i(off)}	input off voltage	V _{CE} = 5 V; I _C = 100 μA	–	–	0.5	V
V _{i(on)}	input on voltage	V _{CE} = 0.3 V; I _C = 1 mA	3	–	–	V
R1	input resistor		70	100	130	k Ω
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	I _E = I _e = 0; V _{CB} = 10 V; f = 1 MHz	–	–	2.5	pF

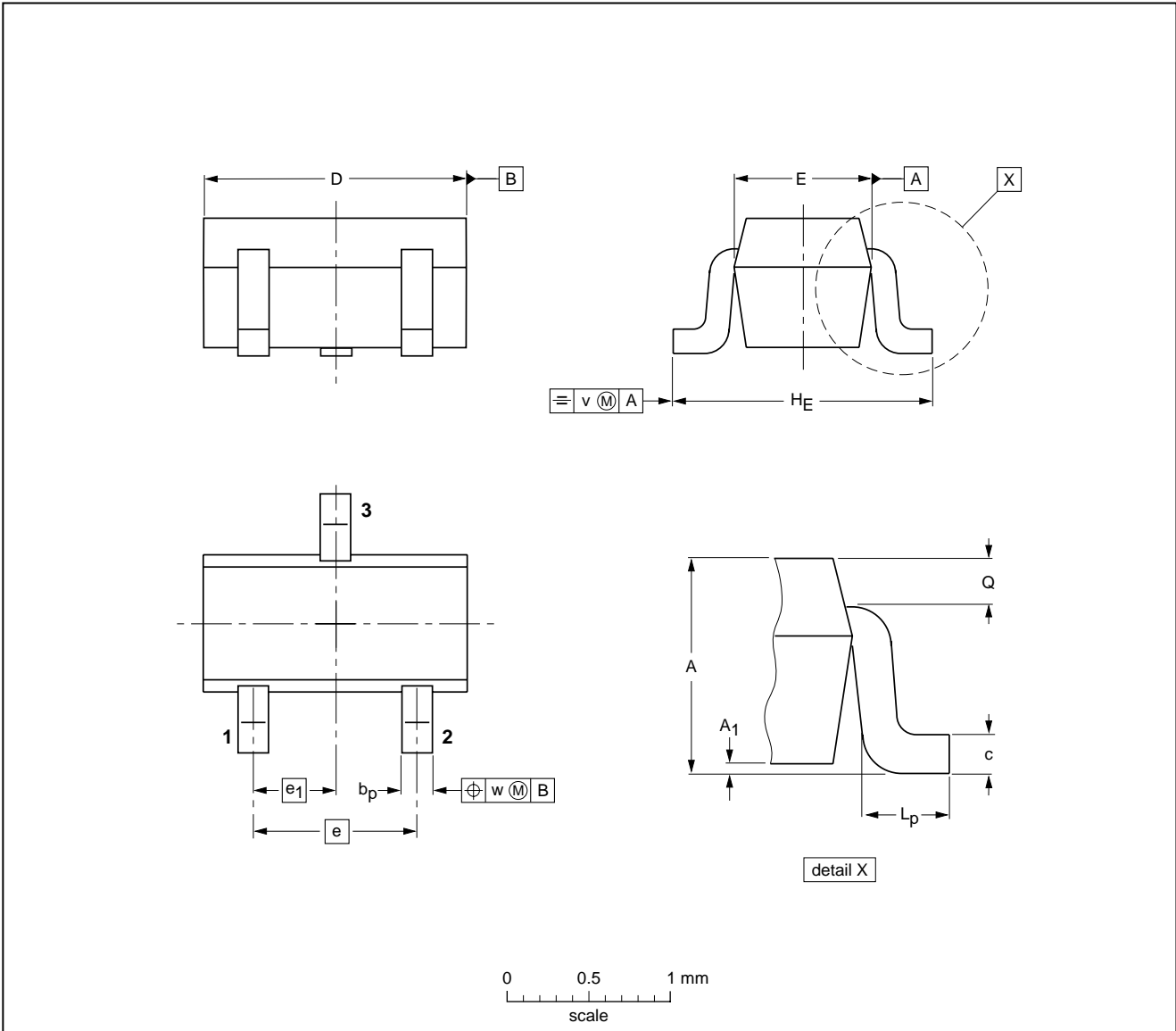
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PDTC115EE

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

NPN resistor-equipped transistor;
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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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NOTES

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Contact information

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